2SB1122

Bipolar Transistor –50V, –1A, Low VCE(sat) PNP Single PCP



http://onsemi.com

Applicaitons

· Voltage regulators relay drivers, lamp drivers, electrical equipment

Features

- Adoption of FBET process
- · Ultrasmall size making it easy to provide high-density hybrid IC's

Specifications

Absolute Maximum Ratings at Ta=25°C

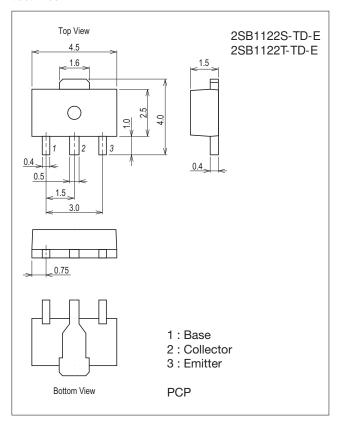
Parameter	Symbol	Conditions	Ratings	Unit
Collector to Base Voltage	V _{CBO}		-60	V
Collector to Emitter Voltage	VCEO		-50	V
Emitter to Base Voltage	VEBO		-5	V
Collector Current	IC		-1	Α
Collector Current (Pulse)	ICP		-2	Α

Continued on next page.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7007B-004



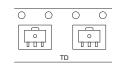
Product & Package Information

• Package : PCP

• JEITA, JEDEC : SC-62, SOT-89, TO-243

• Minimum Packing Quantity: 1,000 pcs./reel

Packing Type: TD Marking





Electrical Connection



Continued from preceding page.

Parameter	Symbol	Conditions	Ratings	Unit
Collector Dissipation	PC	When mounted on ceramic substrate (250mm²×0.8mm)	1.3	W
Junction Temperature	Tj		150	∘C
Storage Temperature	Tstg		-55 to +150	∘C

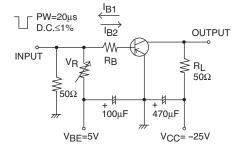
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit	
Farameter	Symbol Conditions		min	typ	max	Unit	
Collector Cutoff Current	ICBO	V _{CB} =-50V, I _E =0A			-100	nA	
Emitter Cutoff Current	IEBO	VEB=-4V, IC=0A			-100	nA	
DO Comment Onlin	hFE1	V _{CE} =-2V, I _C =-100mA	140*		400*		
DC Current Gain	hFE2	V _{CE} =-2V, I _C =-1A	30				
Gain-Bandwidth Product	fŢ	V _{CE} =-10V, I _C =-50mA		150		MHz	
Output Capacitance	Cob	V _{CB} =-10V, f=1MHz		12		рF	
Collector to Emitter Saturation Voltage	V _{CE} (sat)	IC=-500mA, IB=-50mA		-180	-500	mV	
Base to Emitter Saturation Voltage	V _{BE} (sat)	IC=-500mA, IB=-50mA		-0.9	-1.2	V	
Collector to Base Breakdown Voltage	V _(BR) CBO	I _C =-10μA, I _E =0A	-60			V	
Collector to Emitter Breakdown Voltage	V(BR)CEO	IC=-1mA, RBE=∞	-50			V	
Emitter to Base Breakdown Voltage	V(BR)EBO	I _E =-10μA, I _C =0A	-5			V	
Turn-ON Time	ton			40		ns	
Storage Time	t _{stg}	See specified Test Circuit.		300		ns	
Fall Time	tf			30		ns	

*: 2SB1122 is classified by 100mA hFE as follows:

Rank	S	Т
hFE	140 to 280	200 to 400

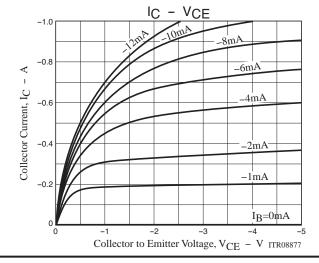
Switching Time Test Circuit

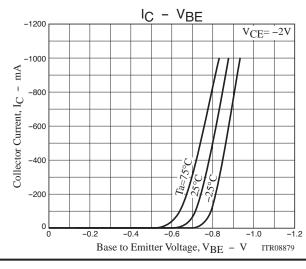


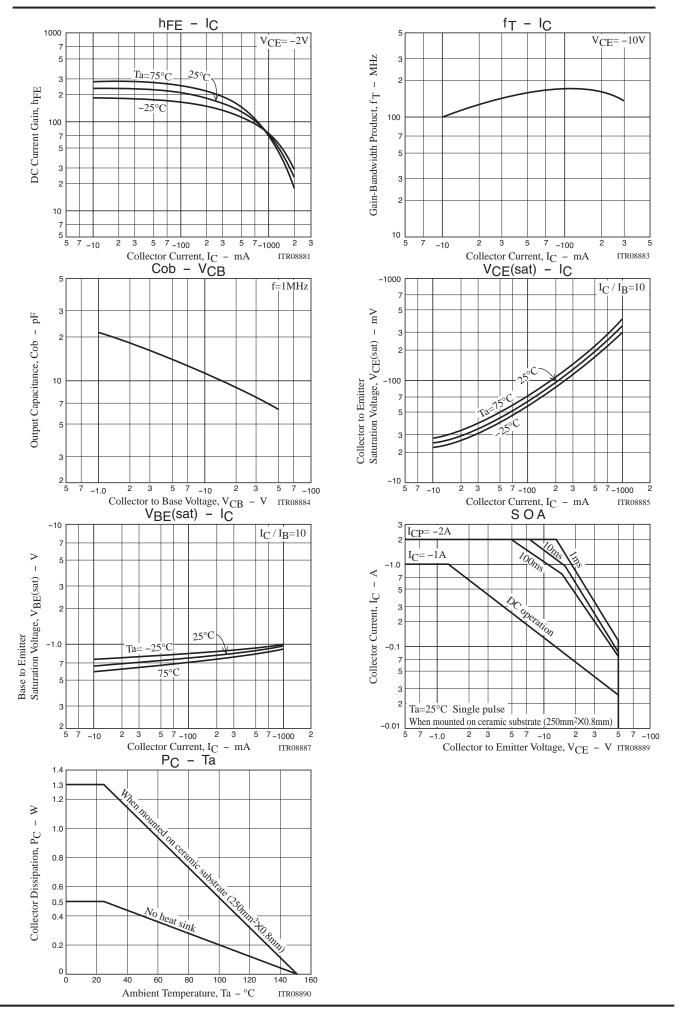
 $I_{C}=10I_{B1}=-10I_{B2}=-500mA$

Ordering Information

Device	Package	Shipping	memo
2SB1122S-TD-E	PCP	1,000pcs./reel	Pb Free
2SB1122T-TD-E	PCP	1,000pcs./reel	Pb Free





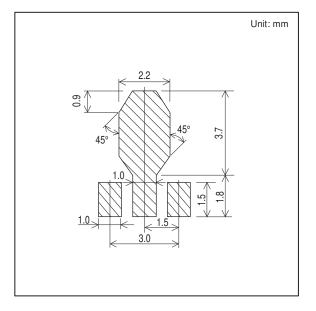


Outline Drawing

2SB1122S-TD-E, 2SB1122T-TD-E

Mass (g) Unit 0.058 mm 4. 5±0. 1 1. 5±0. 1 1. 6±0. 2 2. 5±0. 1 0±0. 0±0.2 $0.4^{+0.08}_{-0.05}$ 0. 4±0.03 0. 5+0. 05 1. 5±0. 2 3. 0±0. 2 0.75 0.10

Land Pattern Example



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*1:Lot indication